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Kind regards,

Team Nexperia



# **PBHV9050T**

500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

Rev. 01 — 16 September 2009

Product data she **Product data sheet** 

### 1. Product profile

### 1.1 General description

PNP high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PMBTA45.

#### 1.2 Features

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified

### 1.3 Applications

- Electronic ballasts
- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Flyback converters
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-	-500	V
$V_{CEO}$	collector-emitter voltage	open base	-	-	-500	V
I <sub>C</sub>	collector current		-	-	-0.15	Α
h <sub>FE</sub>	DC current gain	$V_{CE} = -10 \text{ V};$ $I_{C} = -50 \text{ mA}$	80	160	300	





500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

## 2. Pinning information

Table 2. Pinning

Table 2.	i iiiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	base		_
2	emitter	<u>    3</u>	3 
3	collector	1 2	1 — 2
			sym013

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBHV9050T	-	plastic surface-mounted package; 3 leads	SOT23

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PBHV9050T	LL*

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

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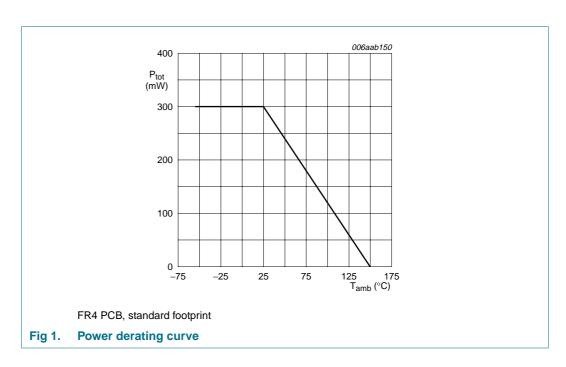
## 500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 5. Limiting values

**Table 5.** Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	-500	V
$V_{CEO}$	collector-emitter voltage	open base	-	-500	V
V <sub>CESM</sub>	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-500	V
$V_{EBO}$	emitter-base voltage	open collector	-	-6	V
I <sub>C</sub>	collector current		-	-0.15	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-0.5	Α
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u>	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



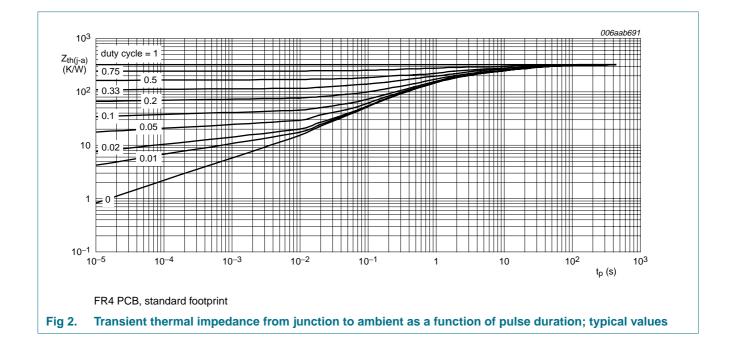
## 500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	417	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	70	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



## 500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

## 7. Characteristics

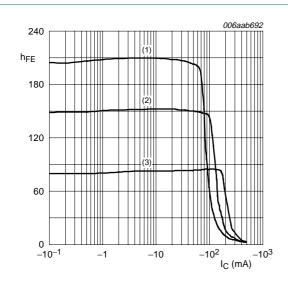
Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -360 \text{ V};$ $I_E = 0 \text{ A}$		-	-	-100	nA
		$V_{CB} = -360 \text{ V};$ $I_E = 0 \text{ A}; T_j = 150 \text{ °C}$		-	-	-10	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -360 \text{ V};$ $V_{BE} = 0 \text{ V}$		-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$		-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -10 \text{ V}$					
		$I_C = -10 \text{ mA}$		100	160	300	
		$I_C = -50 \text{ mA}$	[1]	80	160	300	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -20 \text{ mA};$ $I_B = -2 \text{ mA}$		-	-115	-200	mV
		$I_C = -50 \text{ mA};$ $I_B = -10 \text{ mA}$		-	<b>-95</b>	-200	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -50 \text{ mA};$ $I_B = -10 \text{ mA}$	[1]	-	-0.75	-0.9	V
f <sub>T</sub>	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{E} = -10 \text{ mA};$ $f = 100 \text{ MHz}$		-	50	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -20 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	6	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = -0.5 \text{ V};$ $I_C = i_c = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	170	-	pF
t <sub>d</sub>	delay time	$V_{CC} = -20 \text{ V};$		-	75	-	ns
t <sub>r</sub>	rise time	$I_{C} = -0.05 \text{ A};$ $I_{Bon} = -5 \text{ mA};$		-	1600	-	ns
t <sub>on</sub>	turn-on time	$I_{Bon} = -5 \text{ mA},$ $I_{Boff} = 10 \text{ mA}$		-	1675	-	ns
ts	storage time			-	1200	-	ns
t <sub>f</sub>	fall time			-	550	-	ns
t <sub>off</sub>	turn-off time			-	1750	-	ns

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

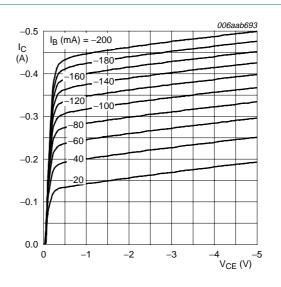




$$V_{CE} = -10 \text{ V}$$

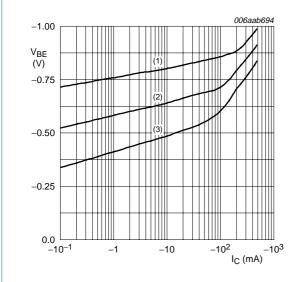
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \,^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



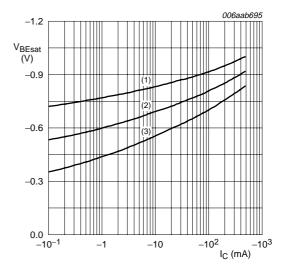
T<sub>amb</sub> = 25 °C

Fig 4. Collector current as a function of collector-emitter voltage; typical values



- $V_{CE} = -10 \text{ V}$
- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values

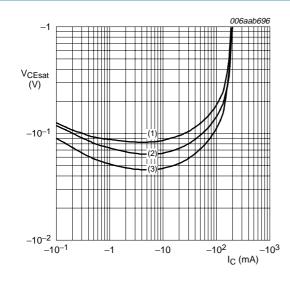


 $I_{\rm C}/I_{\rm B}=5$ 

- (1)  $T_{amb} = -55$  °C
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor



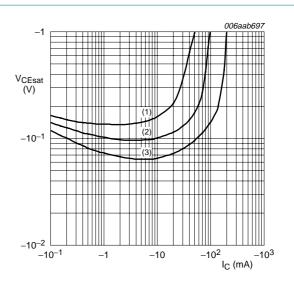
$$I_{\rm C}/I_{\rm B}=5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



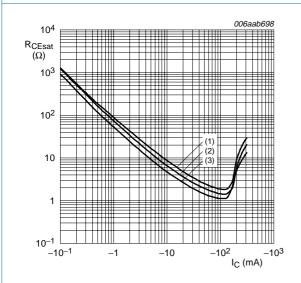
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 20$$

(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



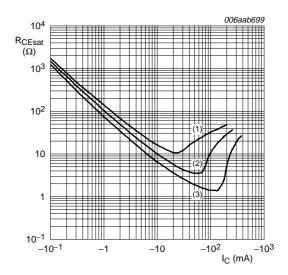
$$I_{\rm C}/I_{\rm B}=5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \,^{\circ}C$$

Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values



(1) 
$$I_C/I_B = 20$$

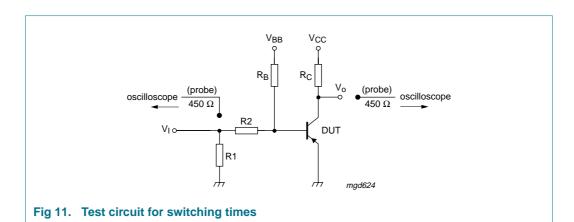
(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

### 500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

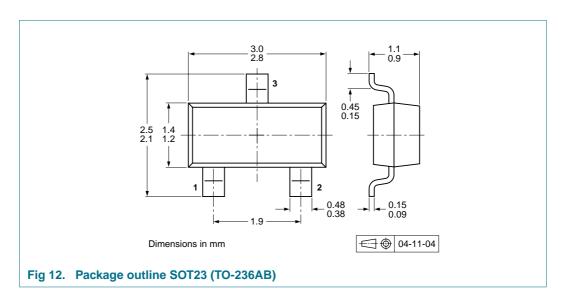
### 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

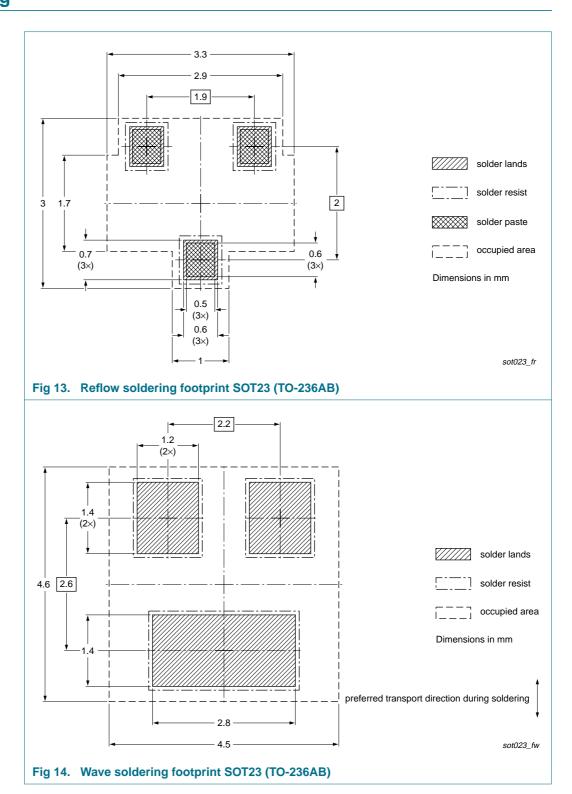
Type number	Package	Description	Packing quantity	
			3000	10000
PBHV9050T	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 14.

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500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

## 11. Soldering



500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 12. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9050T_1	20090916	Product data sheet	-	-

### 500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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**NXP Semiconductors** 

# **PBHV9050T**

## 500 V, 150 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

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